

said p-channel field effect region having a silicon-germanium compound layer formed on said substrate and a silicon epitaxial cap layer formed on said silicon-germanium compound layer,

drain and source regions of said n-channel field effect device being within said silicon epitaxial layer formed on said relax layer, and

drain and source regions of said p-channel field effect device being within said silicon-germanium compound layer formed on said substrate and said silicon epitaxial cap layer formed on said silicon-germanium compound layer.

11. (Amended) The semiconductor device of claim 4 wherein said second silicon epitaxial layer has a thickness of 100 nanometers.

Please cancel claim 12.

Please add new claim 13 as follows:

13. (New) The semiconductor device of claim 4, wherein in cross section said p-channel field effect region silicon germanium layer and said second silicon epitaxial layer occupy substantially the same vertical spacing and position as said n-channel first silicon epitaxial layer.

#### IN THE ABSTRACT OF THE DISCLOSURE

Substitute the attached Abstract for the current Abstract.

#### REMARKS

Claims 4-12 were pending and under consideration.

In the Office Action of October 8, 2002, claims 4-12 were rejected and an objection was raised with respect to the abstract. Claims 4-7, 9 and 11-12 were rejected as being obvious in view of *Kubo et al.* and *Taylor et al.* Claims 8 and 10 were rejected as obvious in view of *Kubo et al.*, *Taylor et al.* and *Imai et al.* Further some informalities were raised. The abstract was deemed too long.

In response, Claims 4 and 11 and the abstract have been amended, Claim 12 has been cancelled in favor of new claim 13.

With respect to the rejection under 35 U.S.C. §112, the claims have been